

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	60970	(polycrystalline near silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 11:39
L2	16168	(polycrystalline near silicon)near film	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 11:39
L3	669	((polycrystalline near silicon) near film) and (crystalliz\$4 near silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 11:40
L4	487	((polycrystalline near silicon) near film) and (crystalliz\$4 near silicon) and irradiat\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 11:40
L5	76	((polycrystalline near silicon) near film) and (crystalliz\$4 near silicon) and irradiat\$4 and (ultraviolet near9 laser)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 11:41
L6	18	((polycrystalline near silicon) near film) and (crystalliz\$4 near silicon) and irradiat\$4 and (ultraviolet near9 laser) and (move\$4 near9 silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 11:42
L7	16	((polycrystalline near silicon) near film) and (crystalliz\$4 near silicon) and irradiat\$4 and (ultraviolet near9 laser) and ((movement or moving or move) near9 silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 12:35

## EAST Search History

L8	4	((polycrystalline near silicon) near film) and (crystalliz\$4 near silicon) and irradiat\$4 and (ultraviolet near9 laser) and ((movement or moving or move) near9 silicon) and (438/166. ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/02 12:37
S1	4	((("6372039") or ("6566683") or ("JP11274095") or ("JP11298005") or ("JP2000-286195") or ("JP2000-035806") or ("JP2001-044120") or ("JP2003-068644"))).PN. or (2003/003222).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/05/01 08:10
S2	2	S1 and (semiconductor or wafer or substrate) and (thin near4 film) and polycrystal\$8 and light and (pulse near4 laser) and irradiat\$4 and silicon and ultraviolet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 08:13
S3	2	S1 and (semiconductor or wafer or substrate) and (thin near4 film) and polycrystal\$8 and light and (pulse near4 laser) and irradiat\$4 and (amorphous near4 silicon) and ultraviolet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 08:13
S4	0	S1 and (semiconductor or wafer or substrate) and (thin near4 film) and polycrystal\$8 and light and (pulse near4 laser) and irradiat\$4 and (amorphous near4 silicon) and ultraviolet and harmoic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 08:14
S5	1	S1 and (semiconductor or wafer or substrate) and (thin near4 film) and polycrystal\$8 and light and (pulse near4 laser) and irradiat\$4 and (amorphous near4 silicon) and ultraviolet and harmonic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 08:22
S6	17	(semiconductor or wafer or substrate) and (thin near4 film) and polycrystalliz\$8 and light and (pulse near4 laser) and irradiat\$4 and (amorphous near4 silicon) and ultraviolet and harmonic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 08:26
S7	0	((2004/0253838A1) or (2004/00474881A1)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/05/01 08:27

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S8	0	2004/0253838	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/05/01 08:27
S9	0	"2004/0253838"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/05/01 08:28
S10	0	2004/0253838	US-PGPUB	OR	OFF	2006/05/01 09:16
S11	266159	(yamazaki et al.inv.)	US-PGPUB	OR	OFF	2006/05/01 09:17
S12	0	2004/02543838A1.pn.	US-PGPUB	OR	OFF	2006/05/01 09:18
S13	0	2004/0253838A1.pn.	US-PGPUB	OR	OFF	2006/05/01 09:18
S14	0	2004/0474881A1.pn.	US-PGPUB	OR	OFF	2006/05/01 09:19